

Taiwan Semiconductor

# **Dual N-Channel MOSFET**

 $30V, 20A, 20m\Omega$ 

#### FEATURES

EMICONDUCTOR

AIWAN

- Fast switching
- 100% avalanche tested
- Pb-free plating
- RoHS compliant
- Halogen-free package

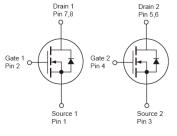
## APPLICATION

- Power Supply
- Motor COntrol

KEY PERFORMANCE PARAMETERS					
PARAM	METER	VALUE	UNIT		
V	V <sub>DS</sub>		V		
D (max)	V <sub>GS</sub> = -10V	20			
$R_{DS(on)}$ (max)	V <sub>GS</sub> = -4.5V	30	mΩ		
Qg		4.1	nC		







Dual N-Channel MOSFET

Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	30	V		
Gate-Source Voltage		V <sub>GS</sub>	±20	V		
Continuous Drain Current (Note 1)	$T_c = 25^{\circ}C$	- I <sub>D</sub>	20	•		
Continuous Drain Current	T <sub>C</sub> = 100°C		13	A		
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	80	А		
Total Power Dissipation @ $T_c = 25^{\circ}C$		P <sub>DTOT</sub>	20	W		
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	14	mJ		
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	17	А		
Operating Junction and Storage Temperatur	re Range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C		

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Case Thermal Resistance	R <sub>eJC</sub>	6.4	°C/W		
Junction to Ambient Thermal Resistance	R <sub>eja</sub>	62	°C/W		

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air

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PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 4)			1			<b>I</b>
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV <sub>DSS</sub>	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	1.2	1.5	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
7 0 4 14 5 4 0 4	$V_{DS} = 30V, V_{GS} = 0V$	_			1	μA
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24V, Tc = 125°C	I <sub>DSS</sub>			10	
	$V_{GS} = 10V, I_D = 10A$	_		17	20	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_{D} = 6A$	$R_{DS(on)}$		23	30	
Forward Transconductance	$V_{DS} = 5V, I_{D} = 6A$	<b>g</b> <sub>fs</sub>		13		S
Dynamic (Note 5)						•
Total Gate Charge		Q <sub>g</sub>		4.1		
Gate-Source Charge	$V_{DS} = 15V, I_D = 8A,$	Q <sub>gs</sub>		1		nC
Gate-Drain Charge	$V_{GS} = 4.5V$	$Q_{gd}$		2.1		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C <sub>iss</sub>		345		
Output Capacitance		C <sub>oss</sub>		55		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		32		
Switching (Note 6)						•
Turn-On Delay Time		t <sub>d(on)</sub>		2.8		
Turn-On Rise Time	$V_{DD} = 15V, I_D = 1A,$ $R_{GEN} = 6\Omega$	t <sub>r</sub>		7.2		
Turn-Off Delay Time		t <sub>d(off)</sub>		15.8		ns
Turn-Off Fall Time		t <sub>f</sub>		4.6		
Source-Drain Diode (Note 4)						•
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	I <sub>S</sub>			20	A
Maximum Pulse Drain-Source Diode Forward Current		I <sub>SM</sub>			80	A
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V <sub>SD</sub>			1	V

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 0.1mH, I\_{AS} = 17A, V\_{DD} = 25V, R\_G = 25\Omega, Starting T\_J = 25  $^{o}C$ 

4. Pulse test: PW  $\leq$  300µs, duty cycle  $\leq$  2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



# **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM200N03DPQ33 RGG	PDFN33	5Kpcs / 13"Reel

Note:

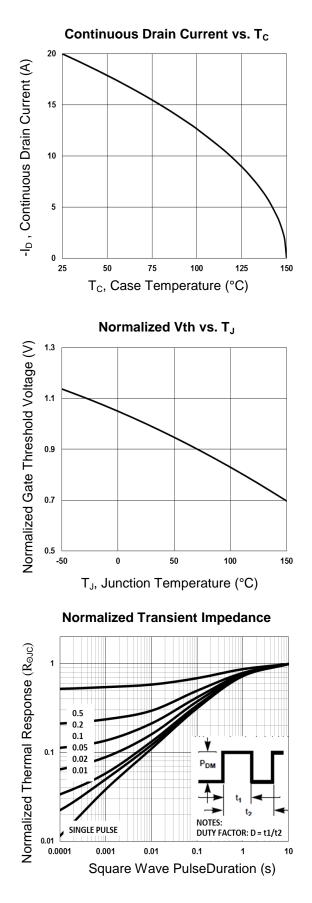
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

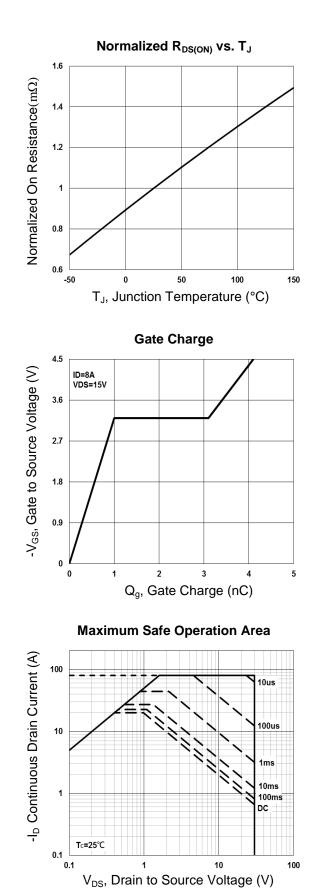
2. Halogen-free according to IEC 61249-2-21 definition



#### **CHARACTERISTICS CURVES**

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

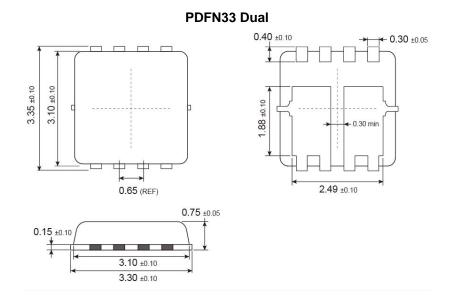




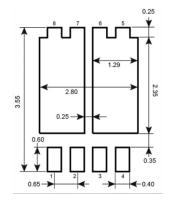




### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



#### SUGGESTED PAD LAYOUT (Unit: Millimeters)



#### **MARKING DIAGRAM**

C	200N03D YML	ו
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Y = Year Code

M = Month Code for Halogen Free Product O =Jan P =Feb Q =Mar R =Apr

- S = May T = Jun U = Jul V = Aug
- W =Sep X =Oct Y =Nov Z =Dec
- L = Lot Code (1~9, A~Z)



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